

April 2012

FDMC8884

N-Channel Power Trench[®] MOSFET 30 V, 15 A, 19 m Ω

Features

- Max $r_{DS(on)} = 19 \text{ m}\Omega$ at $V_{GS} = 10 \text{ V}$, $I_D = 9.0 \text{ A}$
- Max $r_{DS(on)}$ = 30 m Ω at V_{GS} = 4.5 V, I_D = 7.2 A
- High performance technology for extremely low r_{DS(on)}
- Termination is Lead-free and RoHS Compliant

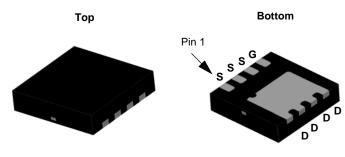


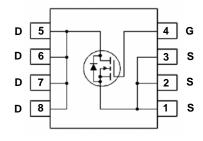
General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance. This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.

Application

- High side in DC DC Buck Converters
- Notebook battery power management
- Load switch in Notebook





MLP 3.3x3.3

MOSFET Maximum Ratings $T_A = 25$ °C unless otherwise noted

Symbol	Parameter		Ratings	Units	
V _{DS}	Drain to Source Voltage			30	V
V_{GS}	Gate to Source Voltage			±20	V
	Drain Current -Continuous (Package limited)	T _C = 25 °C		15	
I _D	-Continuous (Silicon limited)	T _C = 25 °C		24	
	-Continuous	T _A = 25 °C	(Note 1a)	9.0	Α
	-Pulsed			40	
E _{AS}	Single Pulse Avalanche Energy (Note 3)		(Note 3)	24	mJ
Б	Power Dissipation	T _C = 25 °C		18	W
P_{D}	Power Dissipation	T _A = 25 °C	(Note 1a)	2.3	VV
T _J , T _{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case		6.6	°C/W
R _{e.IA}	Thermal Decistance Junction to Ambient		53	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC8884	FDMC8884	MLP 3.3x3.3	13 "	12 mm	3000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	acteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	30			V
ΔBV_{DSS} ΔT_{J}	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, referenced to 25 °C		22		mV/°C
I	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V			1	μА
I _{DSS} Zero Gate Voltage Drain Currer	Zero Gate Voltage Drain Current	T _J = 125 °C			250	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

On Characteristics

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	1.4	1.9	2.5	V
$\Delta V_{GS(th)}$ ΔT_J	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		-6		mV/°C
		$V_{GS} = 10 \text{ V}, I_D = 9.0 \text{ A}$		16	19	
r _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 7.2 \text{ A}$		22	30	mΩ
	$V_{GS} = 10 \text{ V}, I_D = 9.0 \text{ A}, T_J = 125 \text{ °C}$		22	30	1	
g _{FS}	Forward Transconductance	$V_{DD} = 5 \text{ V}, \ I_{D} = 9.0 \text{ A}$		24		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 45.V.V 0.V	513	685	pF
Coss	Output Capacitance	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	110	150	рF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1/11/12	76	115	pF
R_a	Gate Resistance		1.4	2.1	Ω

Switching Characteristics

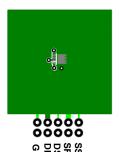
t _{d(on)}	Turn-On Delay Time		6	12	ns
t _r	Rise Time	V _{DD} = 15 V, I _D = 9.0 A,	2	10	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$	15	27	ns
t _f	Fall Time		2	10	ns
0	Total Gate Charge	V _{GS} = 0 V to 10 V	10	14	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0 \text{ V to } 4.5 \text{ V}$ $V_{DD} = 15 \text{ V}$	5.0	7.0	nC
Q_{gs}	Total Gate Charge	I _D = 9.0 A	1.8		nC
Q_{qd}	Gate to Drain "Miller" Charge		2.2		nC

Drain-Source Diode Characteristics

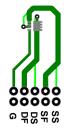
V	Vob Source to Drain Diode Forward voltage	$V_{GS} = 0 \text{ V}, I_S = 9.0 \text{ A}$ (Note 2)		0.86	1.2	\/
V SD		$V_{GS} = 0 \text{ V}, I_{S} = 1.6 \text{ A}$ (Note 2)		0.76	1.2	V
t _{rr}	Reverse Recovery Time	- I _F = 9.0 A, di/dt = 100 A/μs		13	18	ns
Q _{rr}	Reverse Recovery Charge			3	10	nC

NOTES

^{1.} R_{0JA} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{0JC} is guaranteed by design while R_{0CA} is determined by the user's board design.



a. 53 °C/W when mounted on a 1 in² pad of 2 oz copper



b.125 °C/W when mounted on a minimum pad of 2 oz copper

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- 2. Pulse Test: Pulse Width < 300 $\mu s,$ Duty cycle < 2.0 %.
- 3. E_{AS} of 24 mJ is based on starting T_J = 25 $^{\circ}C$, L = 1 mH, I_{AS} = 7 A, V_{DD} = 30 V, V_{GS} = 10 V. 100% test at L = 3 mH, I_{AS} = 4 A .

Typical Characteristics T_J = 25 °C unless otherwise noted

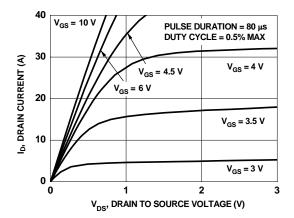


Figure 1. On-Region Characteristics

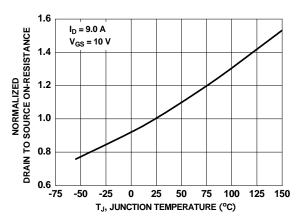


Figure 3. Normalized On-Resistance vs Junction Temperature

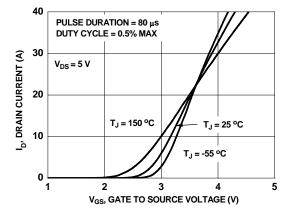


Figure 5. Transfer Characteristics

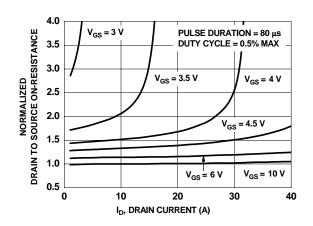


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

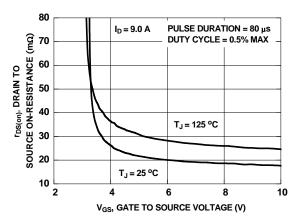


Figure 4. On-Resistance vs Gate to Source Voltage

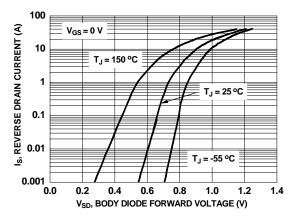


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25$ °C unless otherwise noted

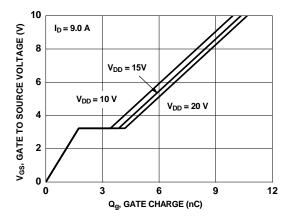


Figure 7. Gate Charge Characteristics

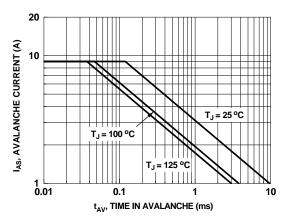


Figure 9. Unclamped Inductive Switching Capability

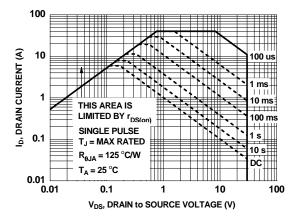


Figure 11. Forward Bias Safe Operating Area

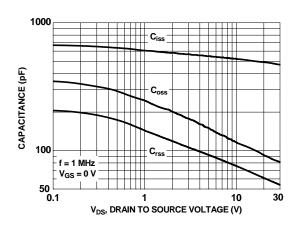


Figure 8. Capacitance vs Drain to Source Voltage

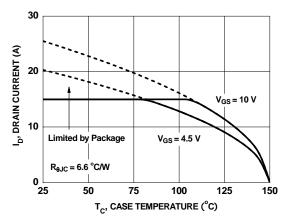


Figure 10. Maximum Continuous Drain Current vs Case Temperature

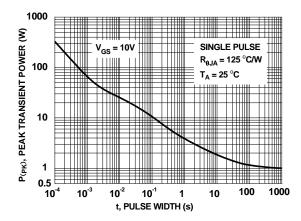


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25$ °C unless otherwise noted

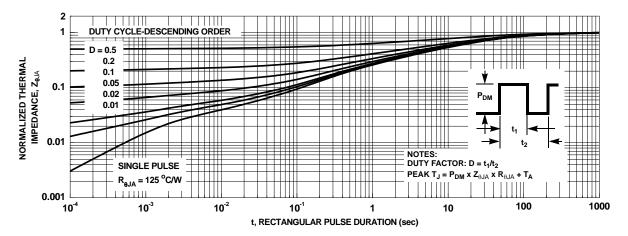
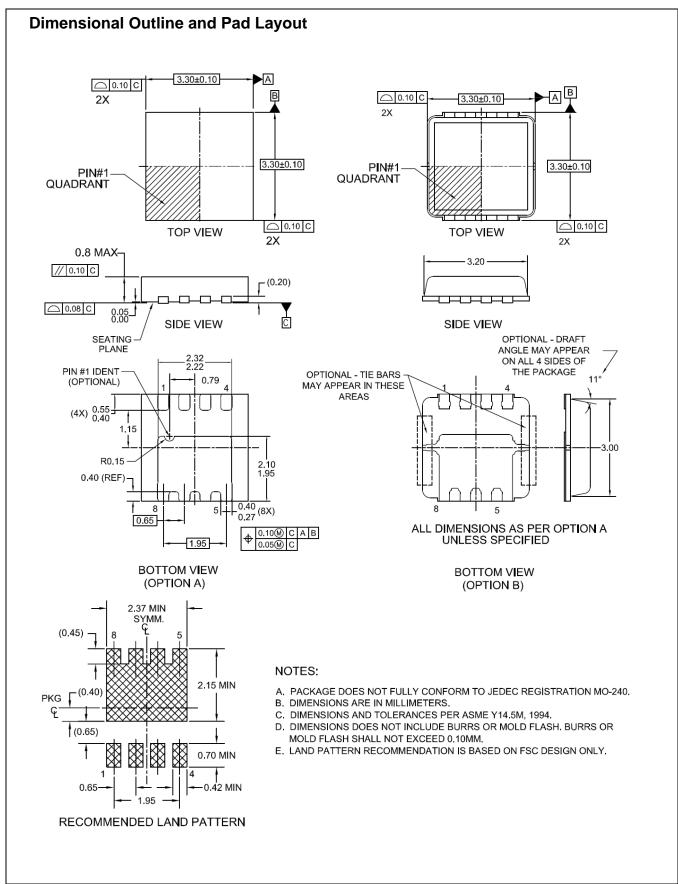


Figure 13. Transient Thermal Response Curve







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